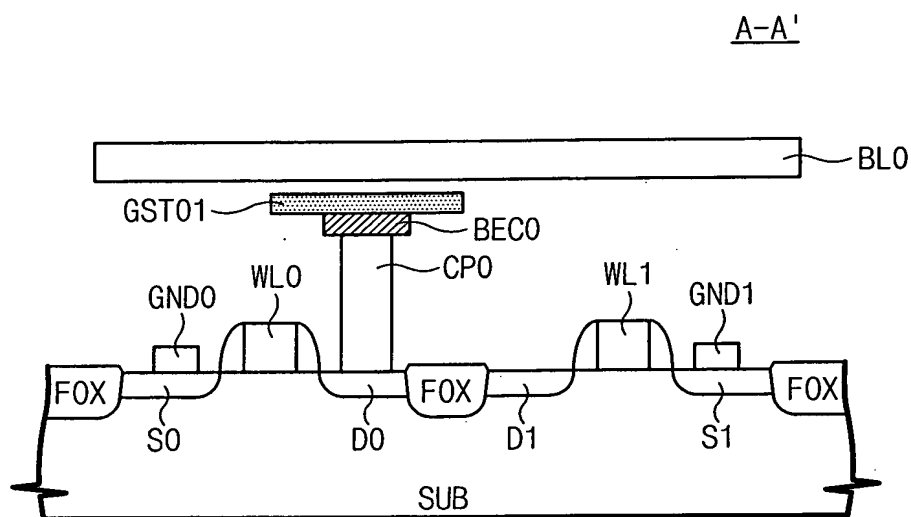


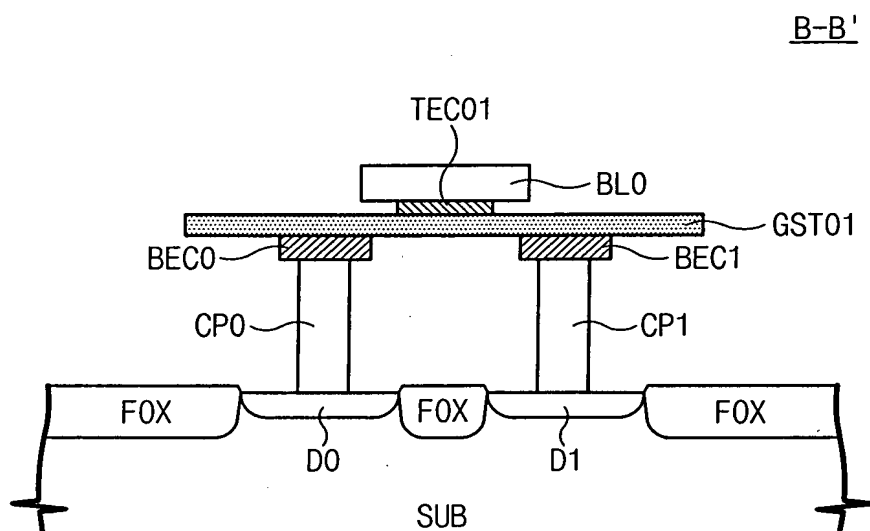


# REPLACEMENT SHEET

## Fig. 8A

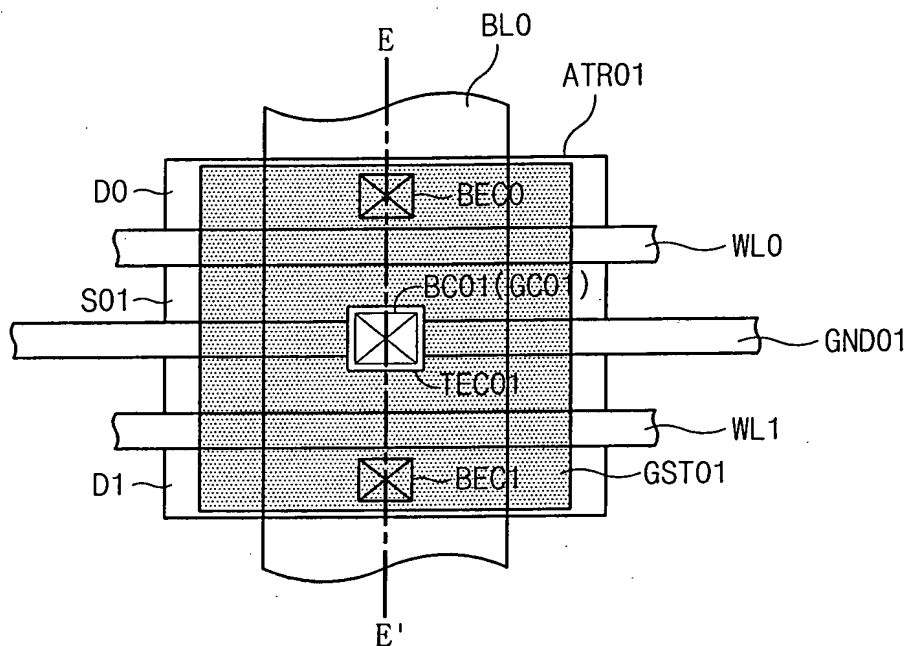


## Fig. 8B

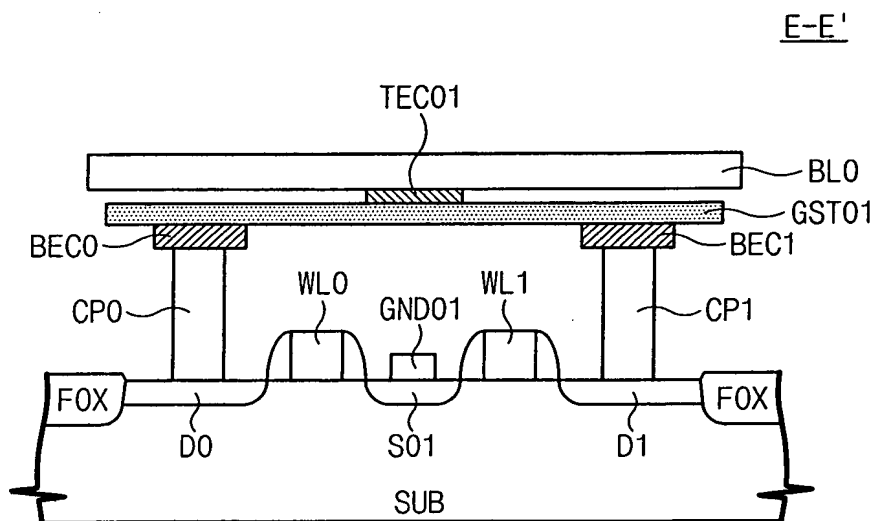


# REPLACEMENT SHEET

## Fig. 11



## Fig. 12



## Fig. 15

Diagram illustrating a cross-sectional view of a semiconductor device 100. The device is built on a substrate (SUB) with a FOX layer. It features two main regions, D0 and D1, separated by a central region S01. Above D0 and D1 are gates CP0 and CP1, respectively, which are connected to a common gate line (GND01) via contacts WLO and WL1. The gates CP0 and CP1 are made of a material labeled GST0 and GST1, respectively, and are separated by a layer labeled BEC0 and BEC1. A top layer labeled BL0 is also present.